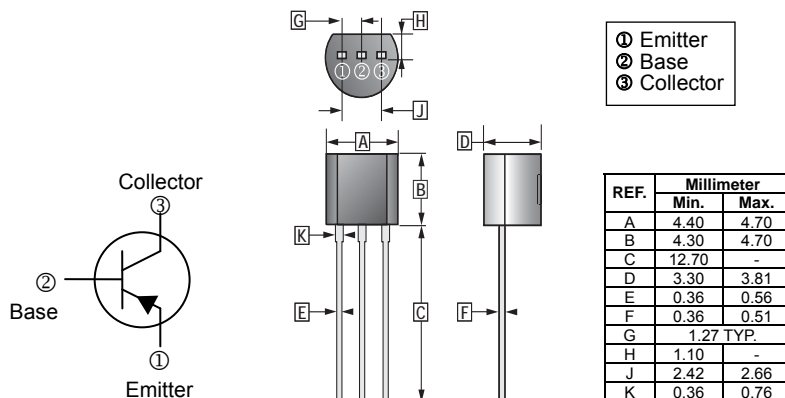


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- General Purpose Amplifier Transistor

TO-92



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	-40	V
Collector to Emitter Voltage	V _{CEO}	-40	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-0.6	A
Collector Power Dissipation	P _C	625	mW
Thermal resistance, junction to ambient	R _{θJA}	200	°C / W
Junction, Storage Temperature	T _J , T _{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to Base Breakdown Voltage	V _{(BR)CBO}	-40	-	-	V	I _C = 0.1mA, I _E = 0A
Collector to Emitter Breakdown Voltage	V _{(BR)CEO} *	-40	-	-	V	I _C = -1mA, I _B = 0A
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	V	I _E = -0.1mA, I _C = 0A
Collector Cut-Off Current	I _{CBO}	-	-	-0.1	µA	V _{CB} = -40V, I _E = 0 A
Emitter Cut-Off Current	I _{EBO}	-	-	-0.1	µA	V _{EB} = -4V, I _C = 0 mA
DC Current Gain	h _{FE} *	30	-	-		V _{CE} = -1V, I _C = -1mA
		50	-	-		V _{CE} = -1V, I _C = -10mA
		50	-	150		V _{CE} = -2V, I _C = -150mA
		20	-	-		V _{CE} = -2V, I _C = -500mA
Collector to Emitter Saturation Voltage	V _{CE(sat)} *	-	-	-0.4	V	I _C = -150mA, I _B = -15mA
		-	-	-0.75		I _C = -500mA, I _B = -50mA
Base to Emitter Saturation Voltage	V _{BE(sat)} *	-0.75	-	-0.95	V	I _C = -150mA, I _B = -15mA
		-	-	-1.3		I _C = -500mA, I _B = -50mA
Collector output Capacitance	C _{ob}	-	-	8.5	pF	V _{CB} = -10V, I _E = 0A, f = 1MHz
Emitter input Capacitance	C _{ib}	-	-	30	pF	V _{EB} = -0.5V, I _C = 0A, f = 1MHz
Transition Frequency	f _T *	150	-	-	MHz	V _{CE} = -10V, I _C = -20mA, f = 100MHz

*Pulse test : Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.